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Sheet 1 of 5

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Application Number	10/654,790
Filing Date	9/4/03
First Named Inventor	Pan
Art Unit	2818
Examiner Name	M. Tran
Attorney Docket Number	

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Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
MH	1	J.L. PAN, J.E. McMANUS, L. GROBER and J.M. WOODWALL, Gallium-arsenide deep-level pin tunnel diode with very negative conductance, Electronics Letters, Sept. 18, 2003, Vol. 39 No. 19	
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MT	41	SOKRATES T. PANTELIDES, The electronic structure of impurities and other point defects in semiconductors, Reviews ofModern Physics, Oct. 1978, pp. 797-858, Vol. 50, No. 4, © 1978 American Physical Society	
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